

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device, including forming a gate electrode or dummy gate on a fin-type silicon layer, introducing an impurity into the fin-type silicon layer with the gate electrode or dummy gate used as mask so as to form first impurity regions, etching the gate electrode or dummy gate so as to form a gate electrode or dummy gate having a reduced size, and introducing an impurity into the fin-type silicon layer with the gate electrode or dummy gate of the reduced size used as a mask so as to form second impurity regions positioned adjacent to the first impurity diffusion regions.